



STB200N6F3, STI200N6F3 STP200N6F3

N-channel 60 V, 3 mΩ, 120 A D²PAK, TO-220, I²PAK
STripFET™ Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)}	I _D	P _w
STB200N6F3	60 V	< 3.5 mΩ	120 A ⁽¹⁾	330 W
STI200N6F3	60 V	< 3.8 mΩ	120 A ⁽¹⁾	330 W
STP200N6F3	60 V	< 3.8 mΩ	120 A ⁽¹⁾	330 W

1. Value limited by wire bonding

- Ultra low on-resistance
- 100% avalanche tested

Application

- Switching applications

Description

This STripFET™ III Power MOSFET technology is among the latest improvements, which have been especially tailored to minimize on-state resistance providing superior switching performance.

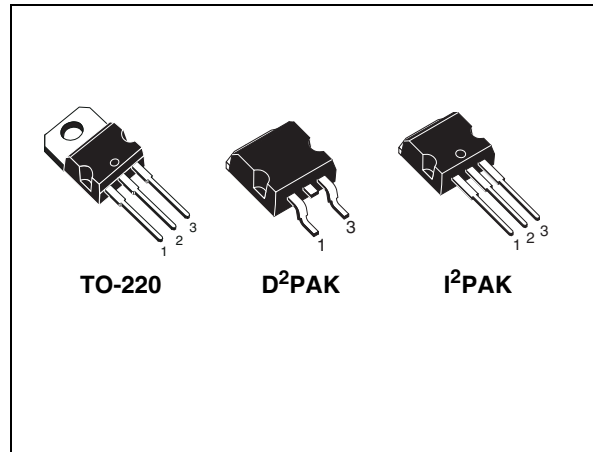


Figure 1. Internal schematic diagram

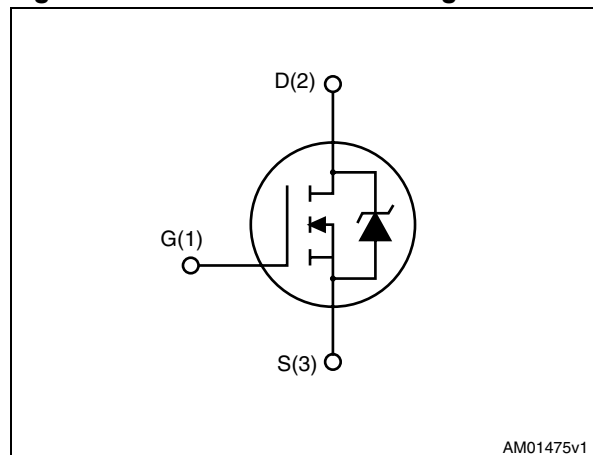


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB200N6F3	200N6F3	D ² PAK	Tape and reel
STI200N6F3	200N6F3	I ² PAK	Tube
STP200N6F3	200N6F3	TO-220	Tube

Contents

1 **Electrical ratings** 3

2 **Electrical characteristics** 4

 2.1 Electrical characteristics (curves) 6

3 **Test circuits** 9

4 **Package mechanical data** 10

5 **Packaging mechanical data** 14

6 **Revision history** 15



1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS}=0$)	60	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	120	A
$I_D^{(1)}$	Drain current (continuous) at $T_C=100^\circ\text{C}$	120	A
$I_{DM}^{(2)}$	Drain current (pulsed)	480	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	330	W
	Derating factor	2.2	W/ $^\circ\text{C}$
$E_{AS}^{(3)}$	Single pulse avalanche energy	918	mJ
T_j T_{stg}	Operating junction temperature storage temperature	-55 To 175	$^\circ\text{C}$

1. Current limited by package.
2. Pulse width limited by safe operating area.
3. Starting $T_j = 25^\circ\text{C}$, $I_D = 60\text{ A}$, $V_{DD} = 35\text{ V}$ (see Figure 18 and Figure 19)

Table 3. Thermal data

Symbol	Parameter	TO-220/l ² PAK	D ² PAK	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.45		$^\circ\text{C/W}$
R_{thj-a}	Thermal resistance junction-ambient max	62.5		$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-ambient max		50	$^\circ\text{C/W}$
T_l	Maximum lead temperature for soldering purpose	300		$^\circ\text{C}$

1. When mounted on 1 inch² FR4 2oz Cu.

2 Electrical characteristics

($T_{CASE}=25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0$	60			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{max rating}$, $V_{DS} = \text{max rating}$, @ 125°C			10 100	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 200	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 60\text{ A}$ D²PAK TO-220, I²PAK		3 3.3	3.5 3.8	$\text{m}\Omega$ $\text{m}\Omega$

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	6265	-	pF
C_{oss}	Output capacitance			1295		pF
C_{rss}	Reverse transfer capacitance			43		pF
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 30\text{ V}$, $I_D = 60\text{ A}$ $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 15, Figure 20)	-	26	-	ns
t_r	Rise time			75		ns
$t_{d(off)}$	Turn-off delay time			86		ns
t_f	Fall time			14		ns
Q_g	Total gate charge	$V_{DD} = 30\text{ V}$, $I_D = 120\text{ A}$, $V_{GS} = 10\text{ V}$, (see Figure 16)	-	101	-	nC
Q_{gs}	Gate-source charge			36		nC
Q_{gd}	Gate-drain charge			25.2		nC

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)		-		120 480	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=120\text{ A}$, $V_{GS}=0$	-		1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=120\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD}=48\text{ V}$, $T_j=150\text{ }^{\circ}\text{C}$ (see Figure 17)	-	67 177.6 5.3		ns nC A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, I²PAK

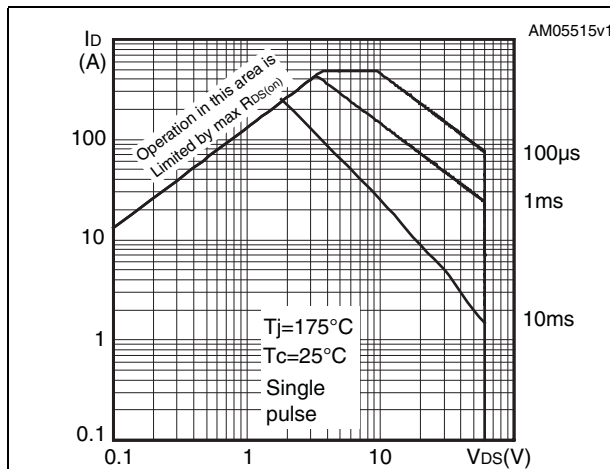


Figure 3. Thermal impedance for TO-220, I²PAK

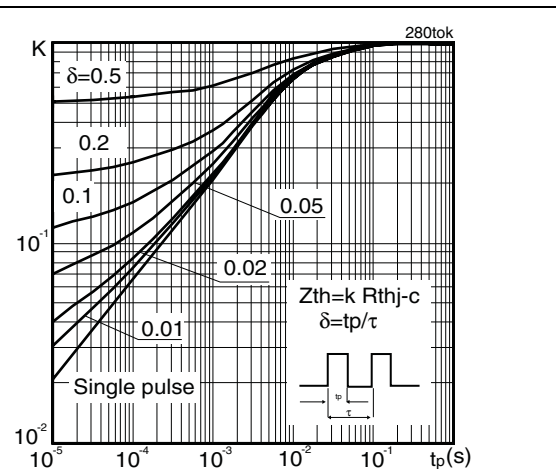


Figure 4. Safe operating area for D²PAK

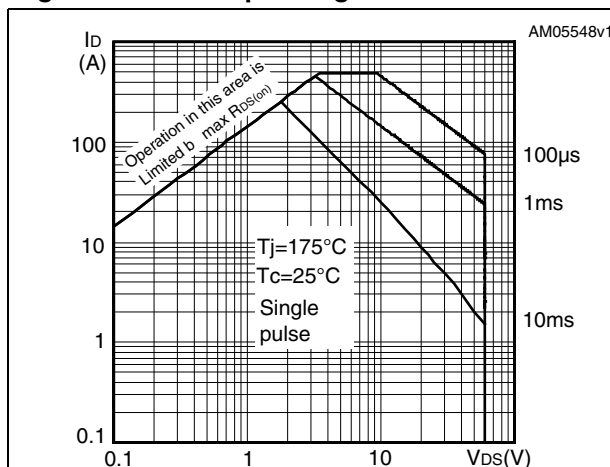


Figure 5. Thermal impedance for D²PAK

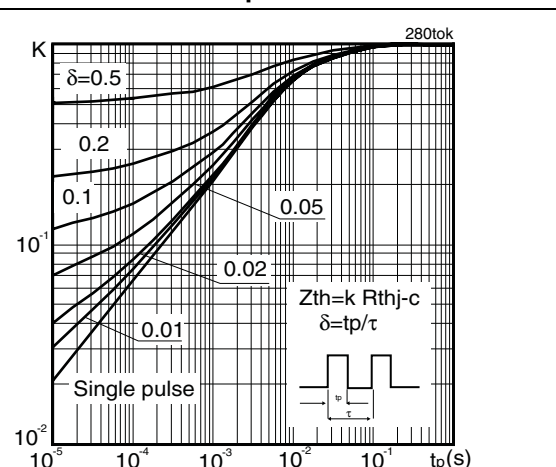


Figure 6. Output characteristics

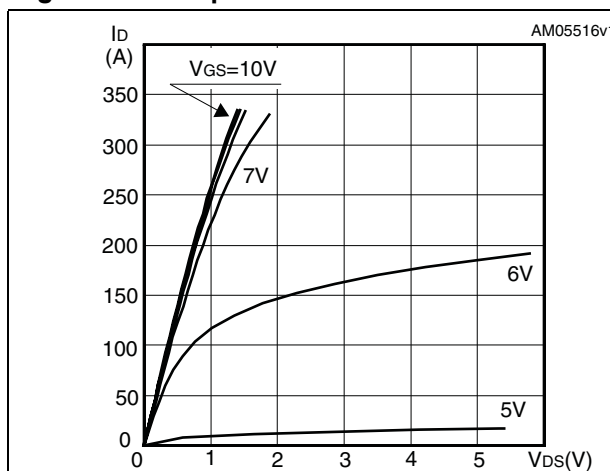


Figure 7. Transfer characteristics

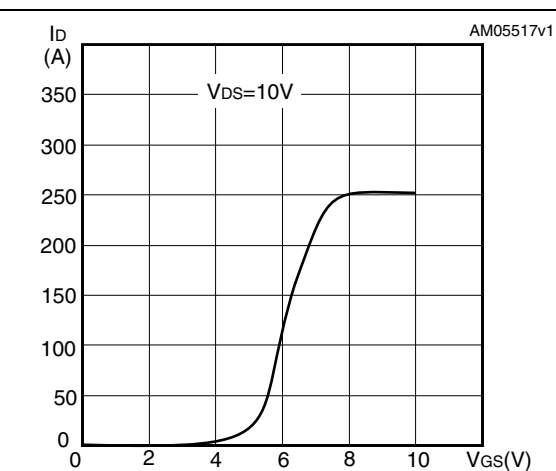


Figure 8. Normalized $B_{V_{DS}}$ vs temperature

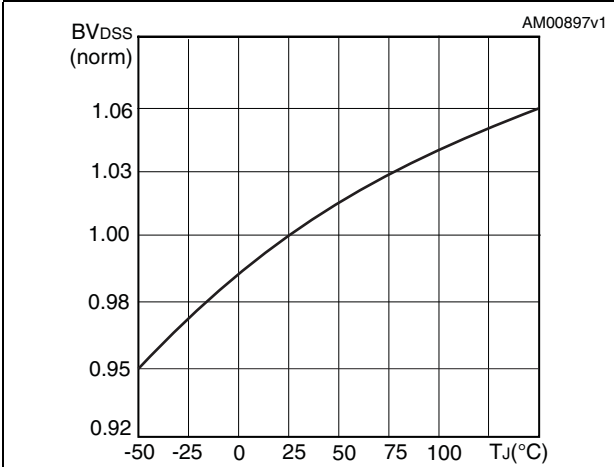


Figure 9. Static drain-source on resistance

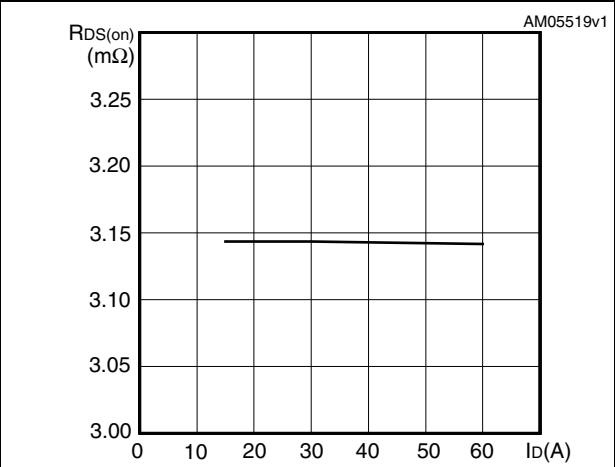


Figure 10. Gate charge vs gate-source voltage

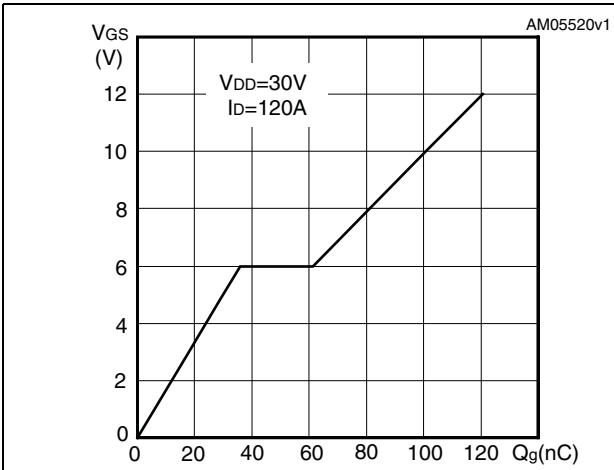


Figure 11. Capacitance variations

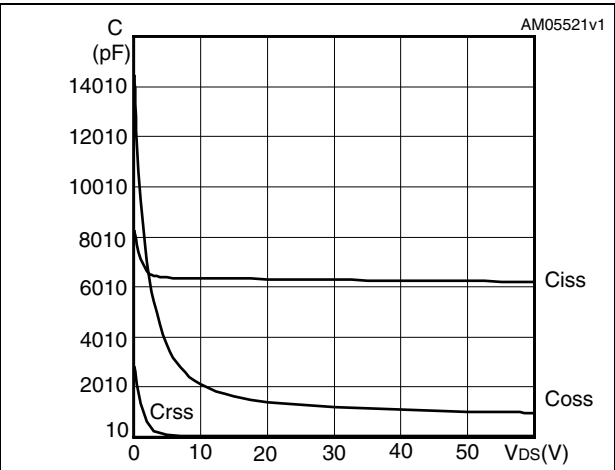


Figure 12. Normalized gate threshold voltage vs temperature

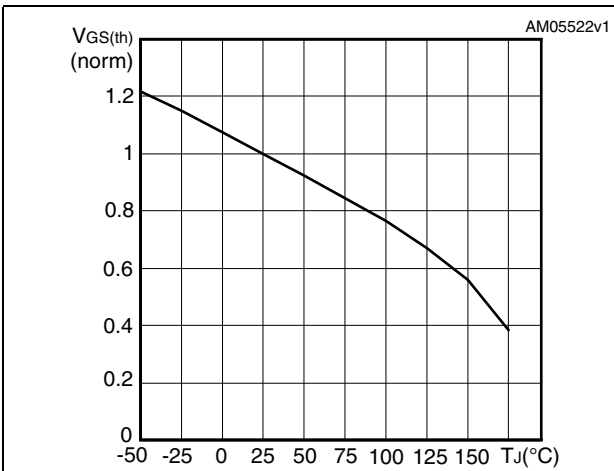


Figure 13. Normalized on resistance vs temperature

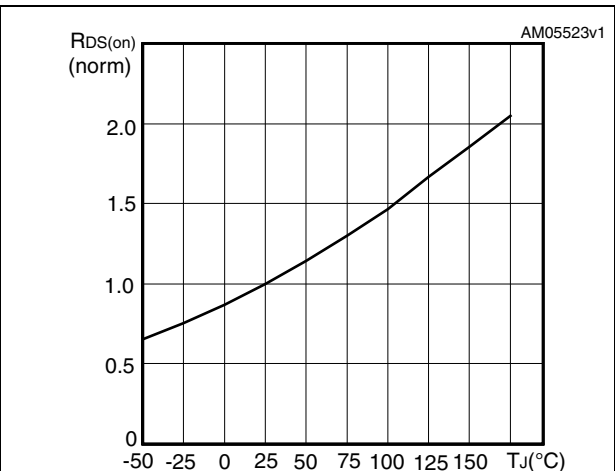
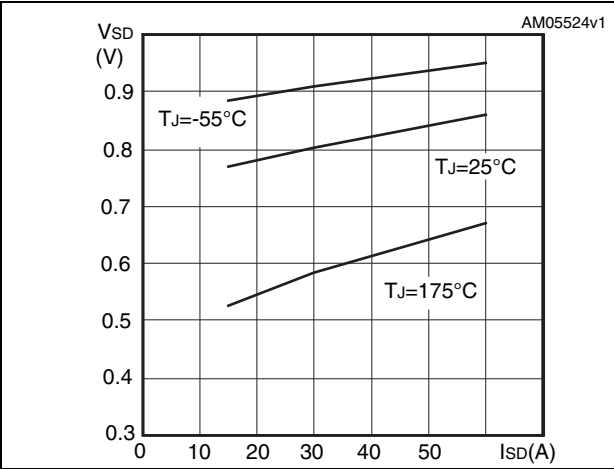


Figure 14. Source-drain diode forward characteristics



3 Test circuits

Figure 15. Switching times test circuit for resistive load

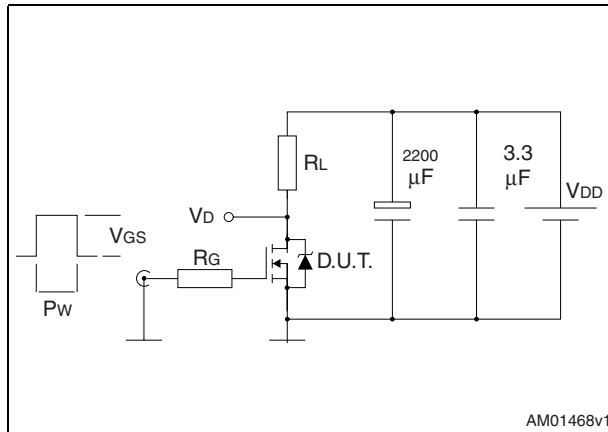


Figure 16. Gate charge test circuit

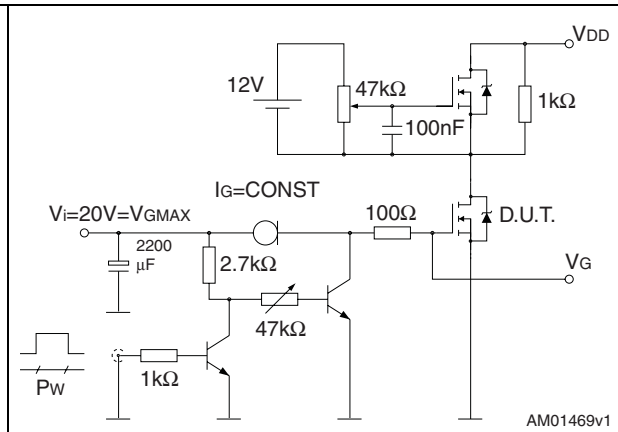


Figure 17. Test circuit for inductive load switching and diode recovery times

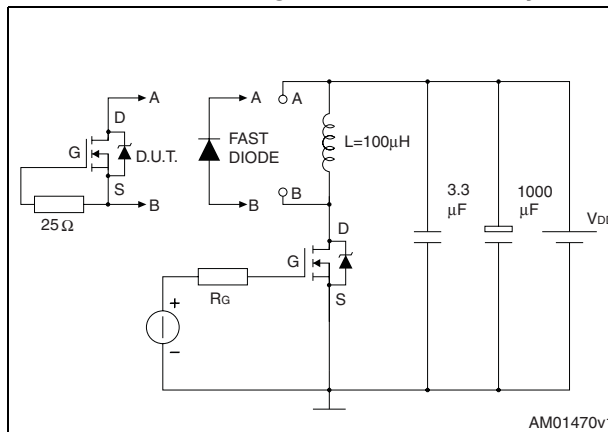


Figure 18. Unclamped inductive load test circuit

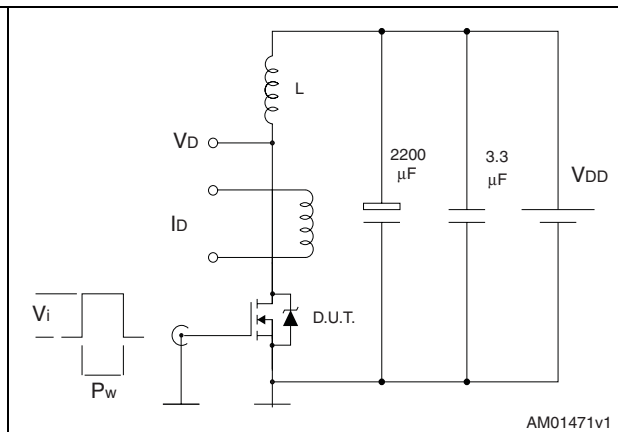


Figure 19. Unclamped inductive waveform

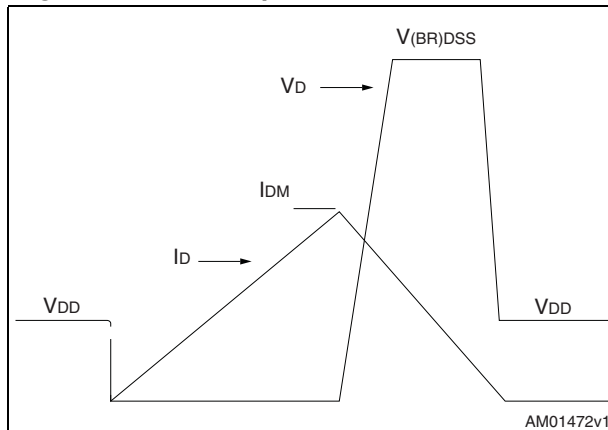
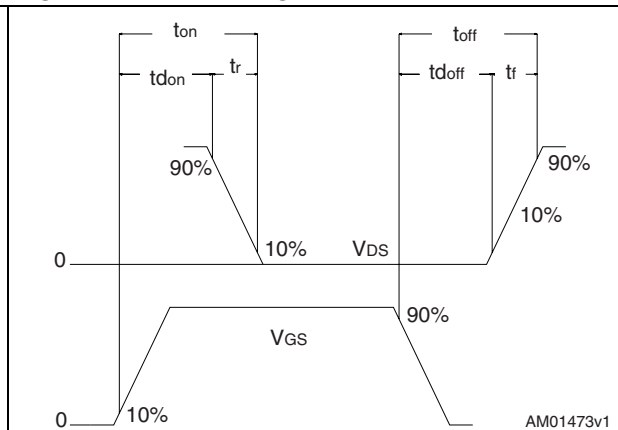


Figure 20. Switching time waveform

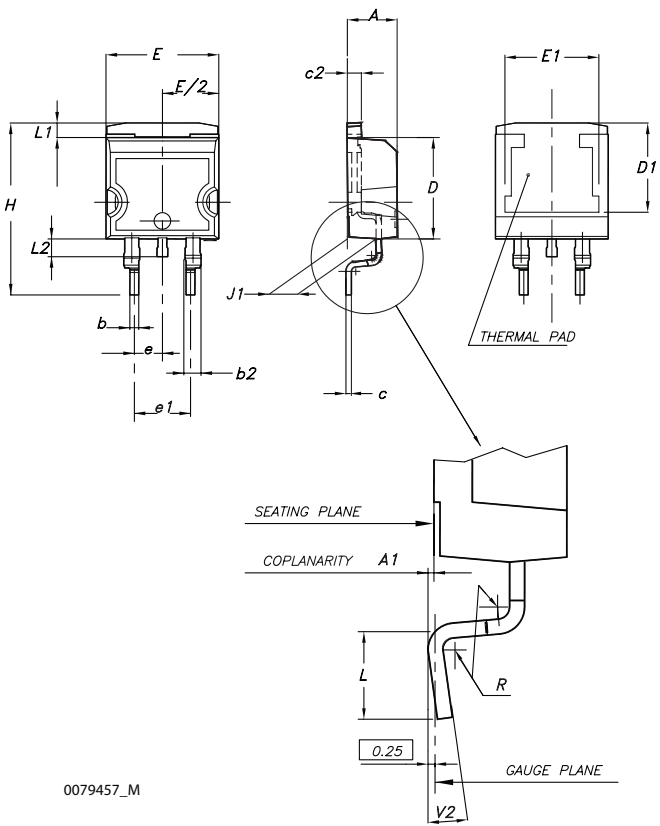


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

D²PAK (TO-263) mechanical data

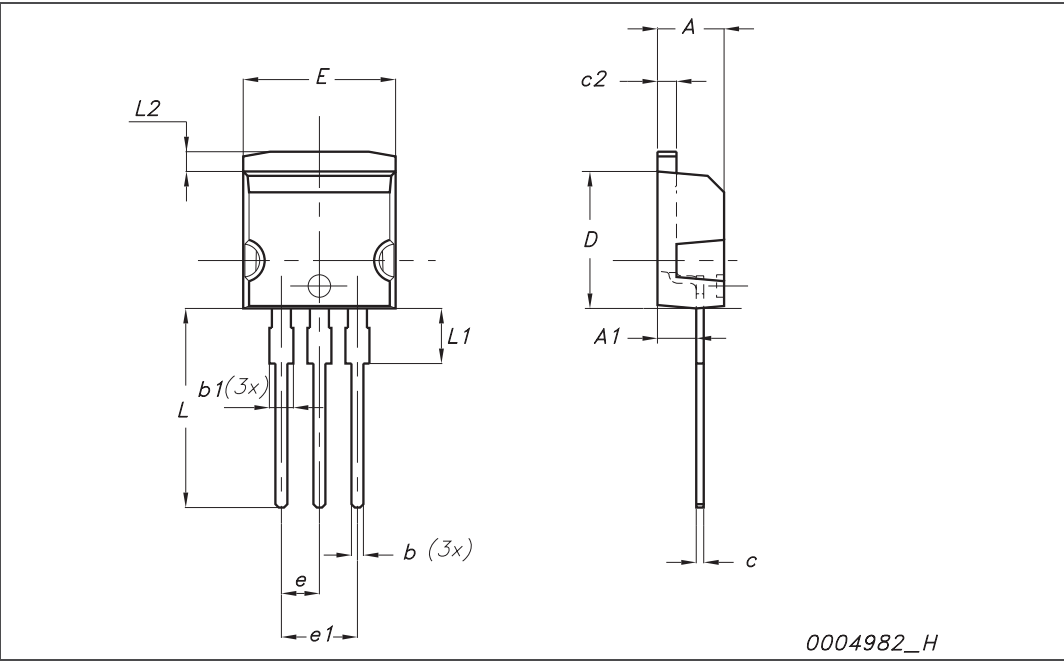
Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



0079457_M

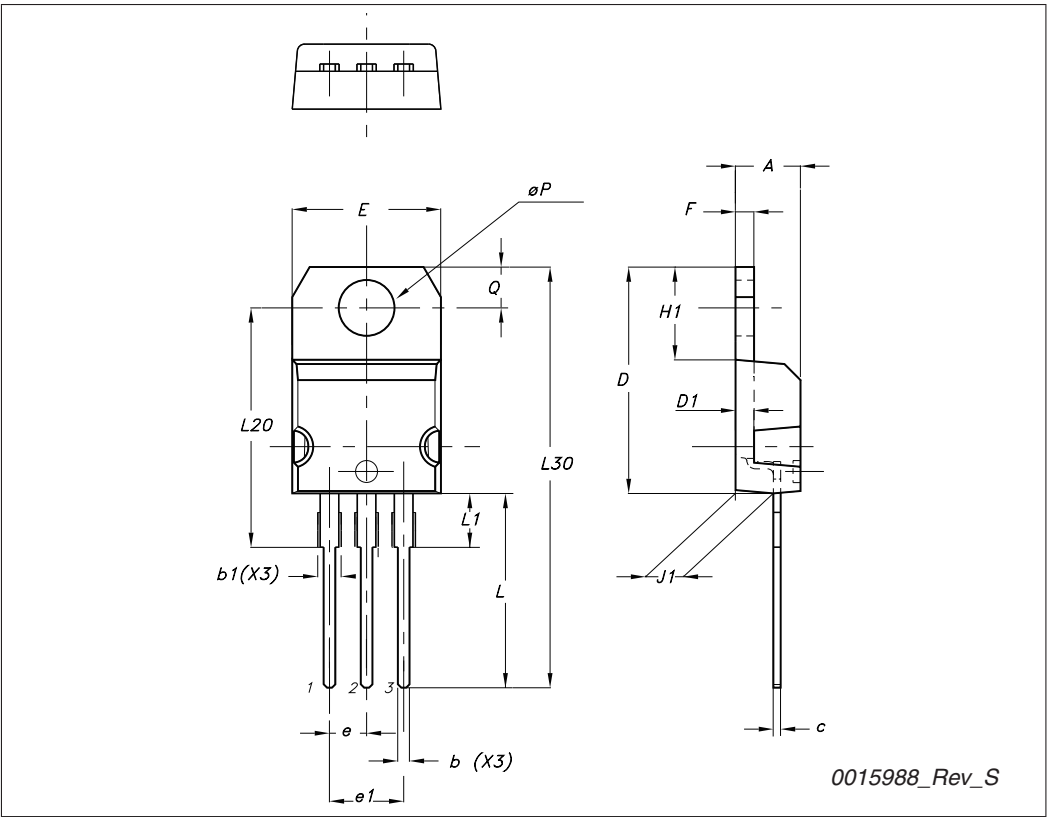
I²PAK (TO-262) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



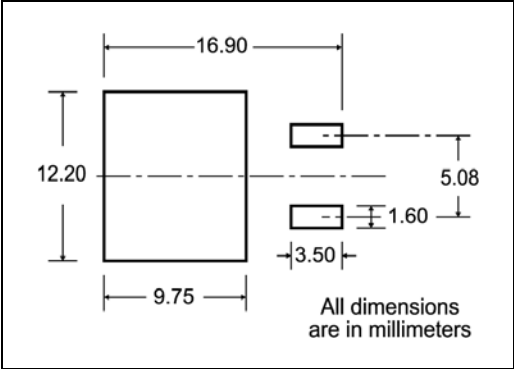
TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

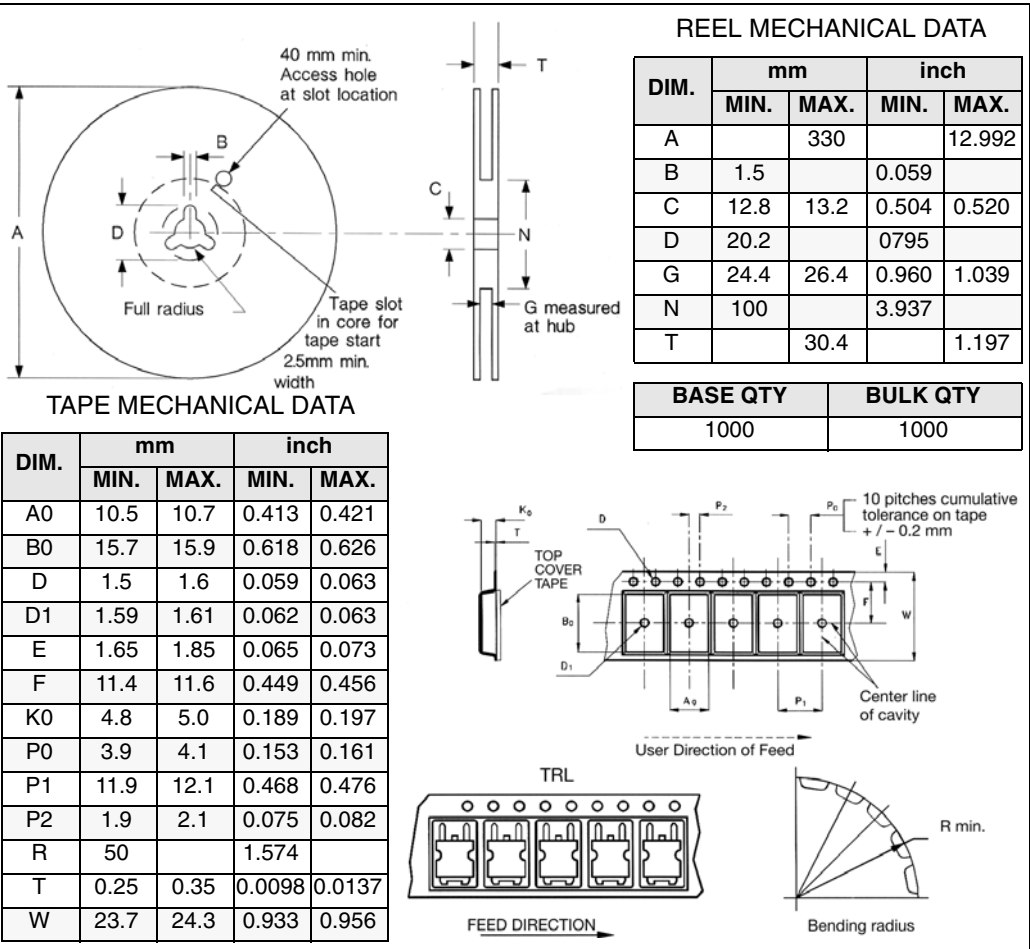


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

6 Revision history

Table 7. Document revision history

Date	Revision	Changes
20-Apr-2009	1	First version.
18-Nov-2009	2	Document status promoted from preliminary data to datasheet.

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